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$\mathcal{N}$ *ational* $\mathcal{S}$ *emiconductor*

LM4250
Programmable Operational Amplifier

General Description

The LM4250 and LM4250C are extremely versatile programmable monolithic operational amplifiers. A single external master bias current setting resistor programs the input bias current, input offset current, quiescent power consumption, slew rate, input noise, and the gain-bandwidth product. The device is a truly general purpose operational amplifier.

The LM4250C is identical to the LM4250 except that the LM4250C has its performance guaranteed over a 0˚C to +70˚C temperature range instead of the −55˚C to +125˚C temperature range of the LM4250.

Features

- ±1V to ±18V power supply operation
- 3 nA input offset current
- Standby power consumption as low as 500 nW
- No frequency compensation required
- Programmable electrical characteristics
- Offset voltage nulling capability
- Can be powered by two flashlight batteries
- Short circuit protection

Connection Diagrams

Metal Can Package
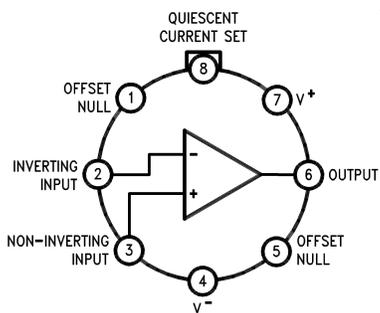
DS009300-2

Top View

Dual-In-Line Package
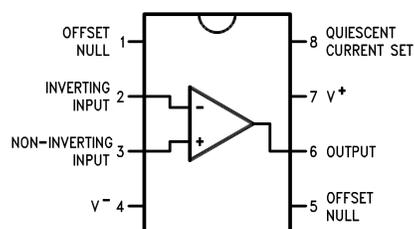
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Top View

X5 Difference Amplifier
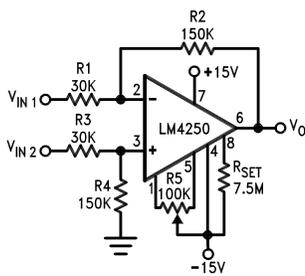
DS009300-3

Quiescent P_D = 0.6 mW

500 Nano-Watt X10 Amplifier
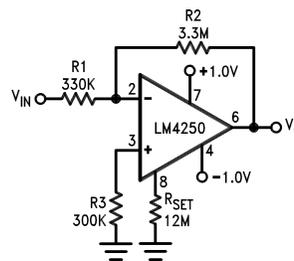
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Quiescent P_D = 500 nW

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

(Note 3)

	LM4250	LM4250C
Supply Voltage	±18V	±18V
Operating Temp. Range	−55˚C ≤ T_A ≤ +125˚C	0˚C ≤ T_A ≤ +70˚C
Differential Input Voltage	±30V	±30V
Input Voltage (Note 2)	±15V	±15V
I_{SET} Current	150 nA	150 nA
Output Short Circuit Duration	Continuous	Continuous
T_{JMAX}		
H-Package	150˚C	100˚C
N-Package		100˚C
J-Package	150˚C	100˚C
M-Package		100˚C
Power Dissipation at T_A = 25˚C		
H-Package (Still Air)	500 mW	300 mW
(400 LF/Min Air Flow)	1200 mW	1200 mW
N-Package		500 mW
J-Package	1000 mW	600 mW
M-Package		350 mW
Thermal Resistance (Typical) θ_{JA}		
H-Package (Still Air)	165˚C/W	165˚C/W
(400 LF/Min Air Flow)	65˚C/W	65˚C/W
N-Package		130˚C/W
J-Package	108˚C/W	108˚C/W
M-Package		190˚C/W
(Typical) θ_{JC}		
H-Package	21˚C/W	21˚C/W
Storage Temperature Range	−65˚C to +150˚C	−65˚C to +150˚C

Soldering Information
  Dual-In-Line Package
    Soldering (10 seconds)   260˚C
  Small Outline Package
    Vapor Phase (60 seconds)   215˚C
    Infrared (15 seconds)   220˚C

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

ESD tolerance (Note 4)   800V

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Note 2: For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.

Note 3: Refer to RETS4250X for military specifications.

Note 4: Human body model, 1.5 kΩ in series with 100 pF.

Resistor Biasing
Set Current Setting Resistor to V⁻

V_S	I_{SET}				
	0.1 µA	0.5 µA	1.0 µA	5 µA	10 µA
±1.5V	25.6 MΩ	5.04 MΩ	2.5 MΩ	492 kΩ	244 kΩ
±3.0V	55.6 MΩ	11.0 MΩ	5.5 MΩ	1.09 MΩ	544 kΩ
±6.0V	116 MΩ	23.0 MΩ	11.5 MΩ	2.29 MΩ	1.14 MΩ
±9.0V	176 MΩ	35.0 MΩ	17.5 MΩ	3.49 MΩ	1.74 MΩ
±12.0V	236 MΩ	47.0 MΩ	23.5 MΩ	4.69 MΩ	2.34 MΩ
±15.0V	296 MΩ	59.0 MΩ	29.5 MΩ	5.89 MΩ	2.94 MΩ

Electrical Characteristics

LM4250 (−55°C ≤ T_A ≤ +125°C unless otherwise specified.) $T_A = T_J$

Parameter	Conditions	V_S = ±1.5V			
		I_{SET} = 1 µA		I_{SET} = 10 µA	
		Min	Max	Min	Max
V_{OS}	R_S ≤ 100 kΩ, T_A = 25°C		3 mV		5 mV
I_{OS}	T_A = 25°C		3 nA		10 nA
I_{bias}	T_A = 25°C		7.5 nA		50 nA
Large Signal Voltage Gain	R_L = 100 kΩ, T_A = 25°C	40k			
	V_O = ±0.6V, R_L = 10 kΩ			50k	
Supply Current	T_A = 25°C		7.5 µA		80 µA
Power Consumption	T_A = 25°C		23 µW		240 µW
V_{OS}	R_S ≤ 100 kΩ		4 mV		6 mV
I_{OS}	T_A = +125°C		5 nA		10 nA
	T_A = −55°C		3 nA		10 nA
I_{bias}			7.5 nA		50 nA
Input Voltage Range		±0.6V		±0.6V	
Large Signal Voltage Gain	V_O = ±0.5V, R_L = 100 kΩ	30k			
	R_L = 10 kΩ			30k	
Output Voltage Swing	R_L = 100 kΩ	±0.6V			
	R_L = 10 kΩ			±0.6V	
Common Mode Rejection Ratio	R_S ≤ 10 kΩ	70 dB		70 dB	
Supply Voltage Rejection Ratio	R_S ≤ 10 kΩ	76 dB		76 dB	
Supply Current			8 µA		90 µA

Parameter	Conditions	V_S = ±15V			
		I_{SET} = 1 µA		I_{SET} = 10 µA	
		Min	Max	Min	Max
V_{OS}	R_S ≤ 100 kΩ, T_A = 25°C		3 mV		5 mV
I_{OS}	T_A = 25°C		3 nA		10 nA
I_{bias}	T_A = 25°C		7.5 nA		50 nA
Large Signal Voltage Gain	R_L = 100 kΩ, T_A = 25°C	100k			
	V_O = ±10V, R_L = 10 kΩ			100k	
Supply Current	T_A = 25°C		10 µA		90 µA
Power Consumption	T_A = 25°C		300 µW		2.7 mW
V_{OS}	R_S ≤ 100 kΩ		4 mV		6 mV
I_{OS}	T_A = +125°C		25 nA		25 nA
	T_A = −55°C		3 nA		10 nA
I_{bias}			7.5 nA		50 nA
Input Voltage Range		±13.5V		±13.5V	

Electrical Characteristics (Continued)

| Parameter | Conditions | $V_S = \pm15V$ | | | |
| | | $I_{SET} = 1 \mu A$ | | $I_{SET} = 10 \mu A$ | |
		Min	Max	Min	Max
Large Signal Voltage Gain	$V_O = \pm10V$, $R_L = 100 k\Omega$	50k			
	$R_L = 10 k\Omega$			50k	
Output Voltage Swing	$R_L = 100 k\Omega$	±12V			
	$R_L = 10 k\Omega$			±12V	
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	76 dB		76 dB	
Supply Current			11 µA		100 µA
Power Consumption			330 µW		3 mW

Electrical Characteristics

LM4250C ($0^\circ C \leq T_A \leq +70^\circ C$ unless otherwise specified.) $T_A = T_J$

| Parameter | Conditions | $V_S = \pm1.5V$ | | | |
| | | $I_{SET} = 1 \mu A$ | | $I_{SET} = 10 \mu A$ | |
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 k\Omega$, $T_A = 25^\circ C$		5 mV		6 mV
I_{OS}	$T_A = 25^\circ C$		6 nA		20 nA
I_{bias}	$T_A = 25^\circ C$		10 nA		75 nA
Large Signal Voltage Gain	$R_L = 100 k\Omega$, $T_A = 25^\circ C$	25k			
	$V_O = \pm0.6V$, $R_L = 10 k\Omega$			25k	
Supply Current	$T_A = 25^\circ C$		8 µA		90 µA
Power Consumption	$T_A = 25^\circ C$		24 µW		270 µW
V_{OS}	$R_S \leq 10 k\Omega$		6.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA
Input Voltage Range		±0.6V		±0.6V	
Large Signal Voltage Gain	$V_O = \pm0.5V$, $R_L = 100 k\Omega$	25k			
	$R_L = 10 k\Omega$			25k	
Output Voltage Swing	$R_L = 100 k\Omega$	±0.6V			
	$R_L = 10 k\Omega$			±0.6V	
Common Mode Rejection Ratio	$R_S \leq 10 k\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 k\Omega$	74 dB		74 dB	
Supply Current			8 µA		90 µA
Power Consumption			24 µW		270 µW

| Parameter | Conditions | $V_S = \pm15V$ | | | |
| | | $I_{SET} = 1 \mu A$ | | $I_{SET} = 10 \mu A$ | |
		Min	Max	Min	Max
V_{OS}	$R_S \leq 100 k\Omega$, $T_A = 25^\circ C$		5 mV		6 mV
I_{OS}	$T_A = 25^\circ C$		6 nA		20 nA
I_{bias}	$T_A = 25^\circ C$		10 nA		75 nA
Large Signal Voltage Gain	$R_L = 100 k\Omega$, $T_A = 25^\circ C$	60k			
	$V_O = \pm10V$, $R_L = 10 k\Omega$			60k	
Supply Current	$T_A = 25^\circ C$		11 µA		100 µA
Power Consumption	$T_A = 25^\circ C$		330 µW		3 mW
V_{OS}	$R_S \leq 100 k\Omega$		6.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA

Electrical Characteristics (Continued)

Parameter	Conditions	$V_S = \pm 15V$			
		$I_{SET} = 1\ \mu A$		$I_{SET} = 10\ \mu A$	
		Min	Max	Min	Max
Input Voltage Range		$\pm 13.5V$		$\pm 13.5V$	
Large Signal Voltage Gain	$V_O = \pm 10V$, $R_L = 100\ k\Omega$	50k			
	$R_L = 10\ k\Omega$			50k	
Output Voltage Swing	$R_L = 100\ k\Omega$	$\pm 12V$			
	$R_L = 10\ k\Omega$			$\pm 12V$	
Common Mode Rejection Ratio	$R_S \leq 10\ k\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10\ k\Omega$	74 dB		74 dB	
Supply Current			11 μA		100 μA
Power Consumption			330 μW		3 mW

Typical Performance Characteristics

Input Bias Current vs I_{SET}

DS009300-15
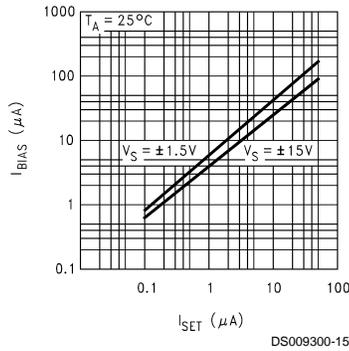
Input Bias Current vs Temperature

DS009300-16
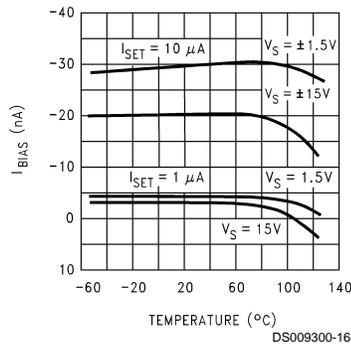
Input Offset Current vs Temperature

DS009300-17
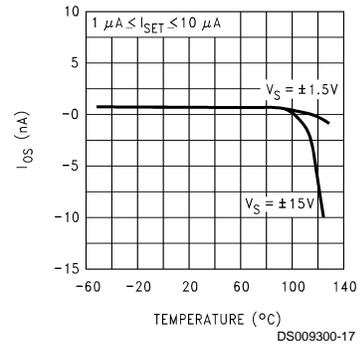
Unnulled Input Offset Voltage Change vs I_{SET}

DS009300-18
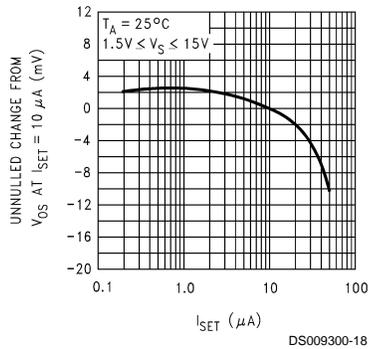
Unnulled Input Offset Voltage Change vs Temperature

DS009300-19
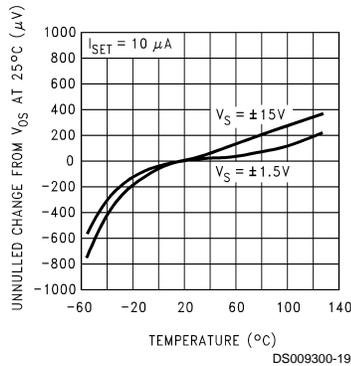
Peak to Peak Output Voltage Swing vs Load Resistance

DS009300-20